CD54/74HC365, CD54/74HCT365, CD54/74HC366

Data sheet acquired from Harris Semiconductor
SCHS180C

November 1997 - Revised October 2003

High Speed CMOS Logic Hex Buffer/Line Driver, Three-State Non-Inverting and Inverting

Features

- **Buffered Inputs**
- **High Current Bus Driver Outputs**
- **Typical Propagation Delay t_{PLH}, t_{PHL} = 8ns at V_{CC} = 5V, C_L = 15pF, T_A = 25^oC**
- **Fanout (Over Temperature Range)**
  - **Standard Outputs . . . . 10 LSTTL Loads**
  - **Bus Driver Outputs . . . . 15 LSTTL Loads**
- **Wide Operating Temperature Range . . . -55^oC to 125^oC**
- **Balanced Propagation Delay and Transition Times**
- **Significant Power Reduction Compared to LSTTL Logic ICs**
- **HC Types**
  - **2V to 6V Operation**
  - **High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V**
- **HCT Types**
  - **4.5V to 5.5V Operation**
  - **Direct LSTTL Input Logic Compatibility, V_{IL}= 0.8V (Max), V_{IH} = 2V (Min)**
  - **CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL}, V_{OH}**

Description

The ’HC365, ’HCT365, and ’HC366 silicon gate CMOS three-state buffers are general purpose high-speed non-inverting and inverting buffers. They have high drive current outputs which enable high speed operation even when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuitry, yet have speeds comparable to low power Schottky TTL circuits. Both circuits are capable of driving up to 15 low power Schottky inputs.

The ’HC365 and ’HCT365 are non-inverting buffers, whereas the ’HC366 is an inverting buffer. These devices have two three-state control inputs ($\overline{OE1}$ and $\overline{OE2}$) which are NORed together to control all six gates.

The ’HCT365 logic families are speed, function and pin compatible with the standard LS logic family.

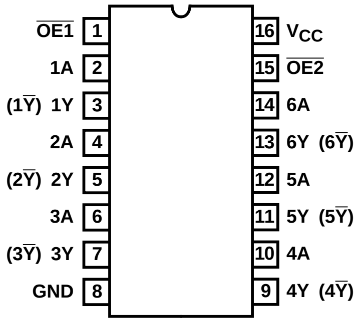
Ordering Information

PART NUMBER	TEMP. RANGE (^oC)	PACKAGE
CD54HC365F3A	-55 to 125	16 Ld CERDIP
CD54HC366F3A	-55 to 125	16 Ld CERDIP
CD54HCT365F3A	-55 to 125	16 Ld CERDIP
CD74HC365E	-55 to 125	16 Ld PDIP
CD74HC365M	-55 to 125	16 Ld SOIC
CD74HC365MT	-55 to 125	16 Ld SOIC
CD74HC365M96	-55 to 125	16 Ld SOIC
CD74HC366E	-55 to 125	16 Ld PDIP
CD74HC366M	-55 to 125	16 Ld SOIC
CD74HC366M96	-55 to 125	16 Ld SOIC
CD74HCT365E	-55 to 125	16 Ld PDIP
CD74HCT365M	-55 to 125	16 Ld SOIC
CD74HCT365MT	-55 to 125	16 Ld SOIC
CD74HCT365M96	-55 to 125	16 Ld SOIC

NOTE: When ordering, use the entire part number. The suffix 96 denotes tape and real. The suffix T denotes a small-quantity reel of 250.

Pinout

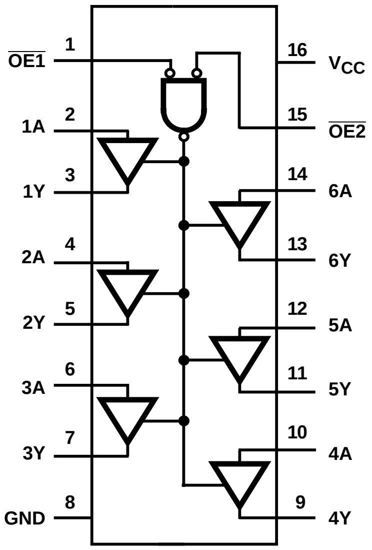
CD54HC365, CD54HCT365, CD54HC366
(CERDIP)
CD74HC365, CD74HCT365, CD74HC366
(PDIP, SOIC)
TOP VIEW



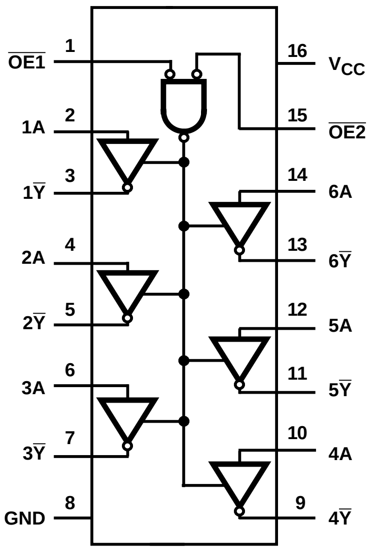
CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper IC Handling Procedures.

Functional Diagrams

HC365, HCT365



HC366

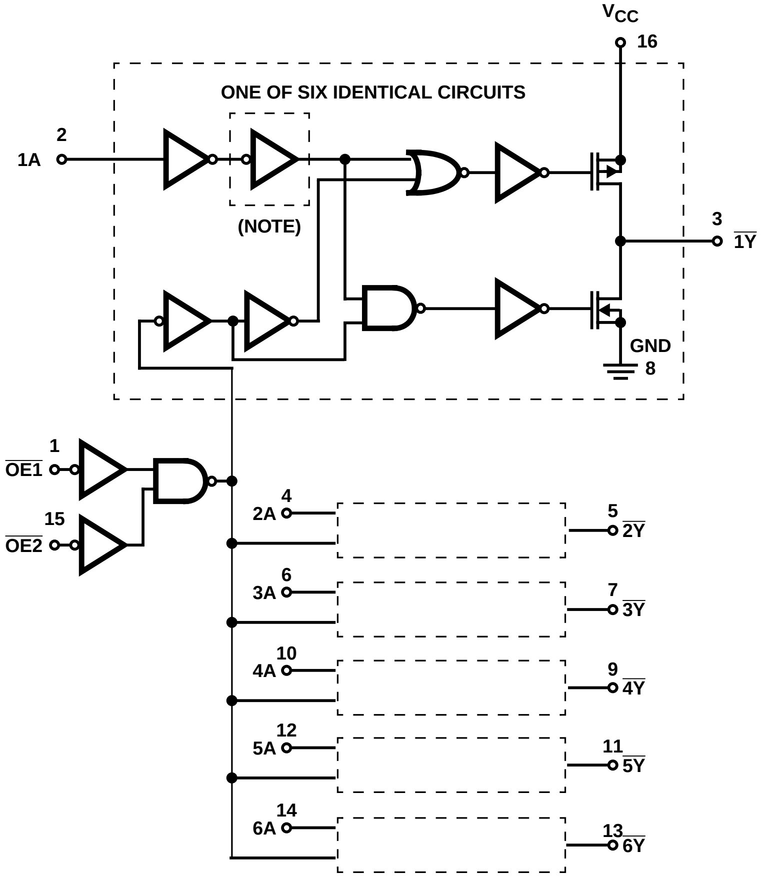


TRUTH TABLE

INPUTS			OUTPUTS (Y)	
$\overline{\text{OE1}}$	$\overline{\text{OE2}}$	A	HC/HCT365	HC366
L	L	L	L	H
L	L	H	H	L
X	H	X	Z	Z
H	X	X	Z	Z

NOTE:
H = High Voltage Level
L = Low Voltage Level
X = Don’t Care
Z = High Impedance (OFF) State

Logic Diagram



NOTE: Inverter not included in HC/HCT365.

FIGURE 1. LOGIC DIAGRAM FOR THE HC/HCT365 AND HC366 (OUTPUTS FOR HC/HCT365 ARE COMPLEMENTS OF THOSE SHOWN, i.e., 1Y, 2Y, ETC.)

Absolute Maximum Ratings

DC Supply Voltage, V_{CC}	-0.5V to 7V
DC Input Diode Current, I_{IK}	
For V_I < -0.5V or V_I > V_{CC} + 0.5V	±20mA
DC Output Diode Current, I_{OK}	
For V_O < -0.5V or V_O > V_{CC} + 0.5V	±20mA
DC Drain Current, per Output, I_O	
For -0.5V < V_O < V_{CC} + 0.5V	±35mA
DC Output Source or Sink Current per Output Pin, I_O	
For V_O > -0.5V or V_O < V_{CC} + 0.5V	±25mA
DC V_{CC} or Ground Current, I_{CC}	±50mA

Operating Conditions

Temperature Range, T_A	-55^{o}C to 125^{o}C
Supply Voltage Range, V_{CC}	
HC Types	2V to 6V
HCT Types	4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O	0V to V_{CC}
Input Rise and Fall Time	
2V	1000ns (Max)
4.5V	500ns (Max)
6V	400ns (Max)

Thermal Information

Thermal Resistance (Typical, Note 1)	θ_{JA} (^{o}C/W)
E (PDIP) Package	67
M (SOIC) Package	73
Maximum Junction Temperature	150^{o}C
Maximum Storage Temperature Range	-65^{o}C to 150^{o}C
Maximum Lead Temperature (Soldering 10s)	300^{o}C
(SOIC - Lead Tips Only)	

CAUTION: Stresses above those listed in “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. The package thermal impedance is calculated in accordance with JESD 51-7.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25^{o}C			-40^{o}C TO 85^{o}C		-55^{o}C TO 125^{o}C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	2	-	-	0.1	-	0.1	-	0.1	V
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	6	-	-	8	-	80	-	160	µA

DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS			25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)	V_{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Three-State Leakage Current	I_{OZ}	V_{IL} or V_{IH}	V_O = V_{CC} or GND	6	-	-	±0.5	-	±5.0	-	±10	µA
HCT TYPES												
High Level Input Voltage	V_{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V_{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I_I	V_{CC} to GND	0	5.5	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I_{CC}	V_{CC} or GND	0	5.5	-	-	8	-	80	-	160	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load (Note 2)	ΔI_{CC}	V_{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA
Three-State Leakage Current	I_{OZ}	V_{IL} or V_{IH}	V_O = V_{CC} or GND	5.5	-	-	±0.5	-	±5.0	-	±10	µA

NOTE:

2. For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
$\overline{OE1}$	0.6
All Others	0.55

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., 360µA max at 25°C.

Switching Specifications - HC/HCT365 Input t_r, t_f = 6ns

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
HC TYPES								
Propagation Delay, Data to Outputs HC/HCT365	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	105	130	160	ns
			4.5	-	21	26	32	ns
			6	-	18	22	27	ns
		C_L = 15pF	5	8	-	-	-	ns

Switching Specifications - HC/HCT365 Input t_r, t_f = 6ns **(Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
Propagation Delay, Data to Outputs HC366	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	110	140	165	ns
			4.5	-	22	28	33	ns
			6	-	19	24	28	ns
		C_L = 15pF	5	9	-	-	-	ns
Propagation Delay, Output Enable and Disable to Outputs	t_{PLH}, t_{PHL}	C_L = 50pF	2	-	150	190	225	ns
			4.5	-	30	38	45	ns
			6	-	26	33	38	ns
		C_L = 15pF	5	12	-	-	-	ns
Output Transition Time	t_{TLH}, t_{THL}	C_L = 50pF	2	-	60	75	90	ns
			4.5	-	12	15	18	ns
			6	-	10	13	15	ns
Input Capacitance	C_I	-	-	-	10	10	10	pF
Three-State Output Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 3, 4)	C_{PD}	-	5	40	-	-	-	pF
HCT TYPES								
Propagation Delay, Data to Outputs HC/HCT365	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	25	31	38	ns
		C_L = 15pF	5	9	-	-	-	ns
Propagation Delay, Data to Outputs HC366	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	27	34	41	ns
		C_L = 15pF	5	11	-	-	-	ns
Propagation Delay, Output Enable and Disable to Outputs	t_{PLH}, t_{PHL}	C_L = 50pF	4.5	-	35	44	53	ns
		C_L = 15pF	5	14	-	-	-	ns
Output Transition Time	t_{TLH}, t_{THL}	C_L = 50pF	4.5	-	12	15	18	ns
Input Capacitance	C_{IN}	-	-	-	10	10	10	pF
Three-State Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 3, 4)	C_{PD}	-	5	42	-	-	-	pF

NOTES:

3. C_{PD} is used to determine the dynamic power consumption, per buffer.
4. $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms

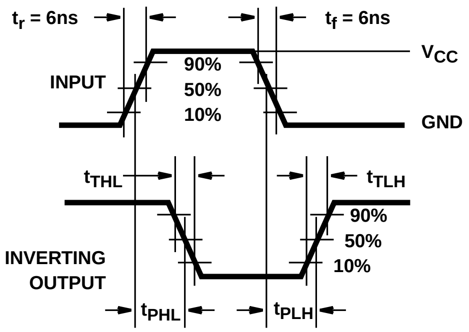


FIGURE 2. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

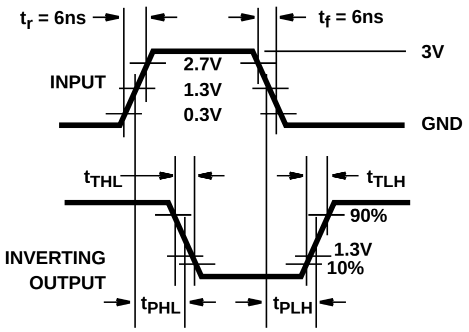


FIGURE 3. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

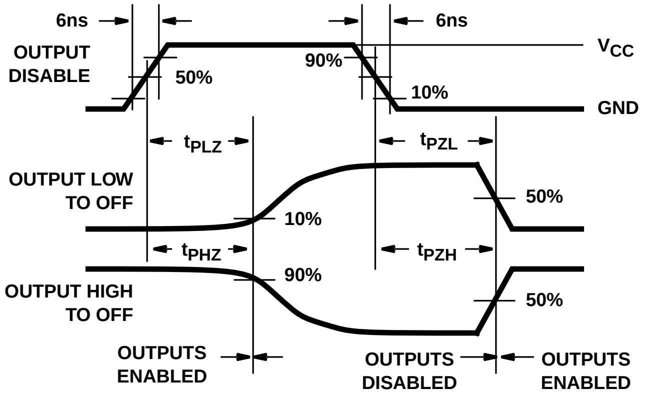


FIGURE 4. HC THREE-STATE PROPAGATION DELAY WAVEFORM

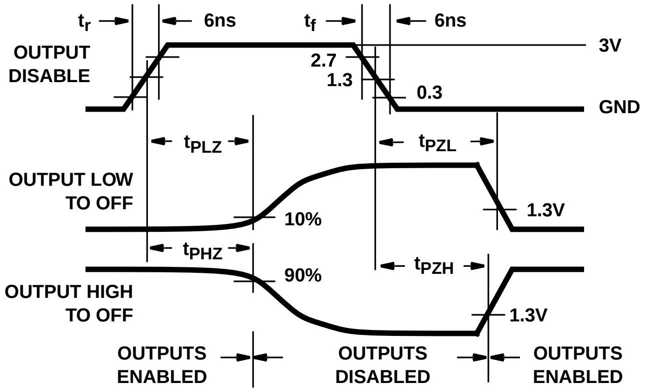
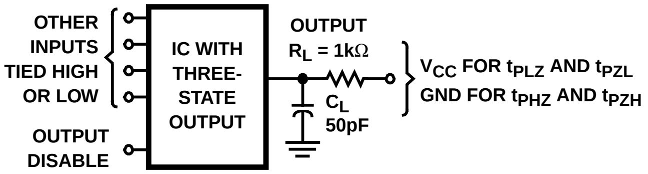


FIGURE 5. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output R_L = 1kΩ to V_{CC}, C_L = 50pF.

FIGURE 6. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT